Fig. 1 PRIOR ART

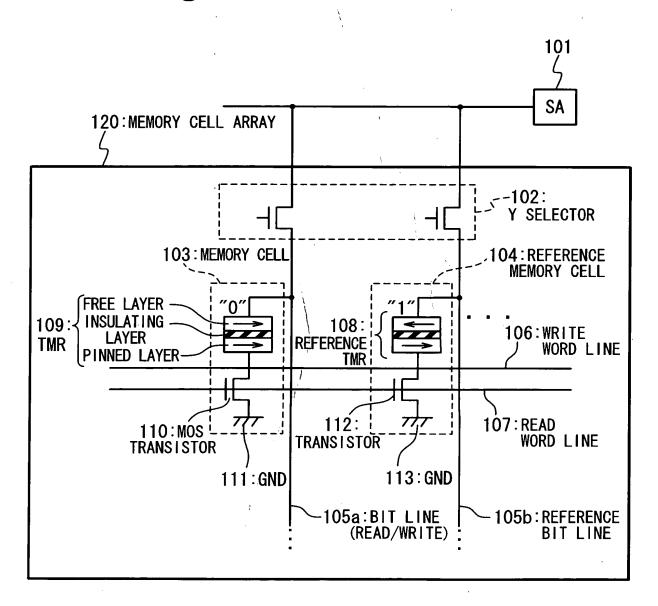


Fig. 2 PRIOR ART

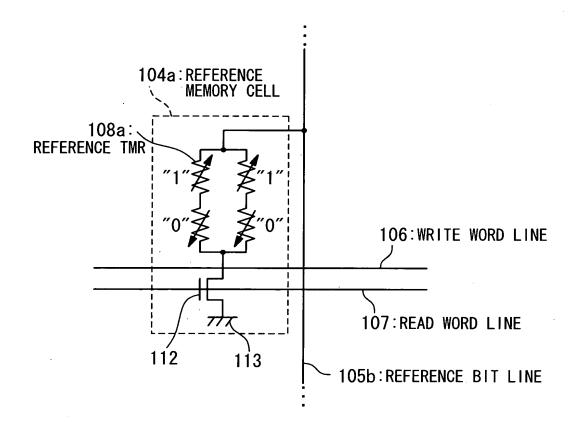


Fig. 3 PRIOR ART

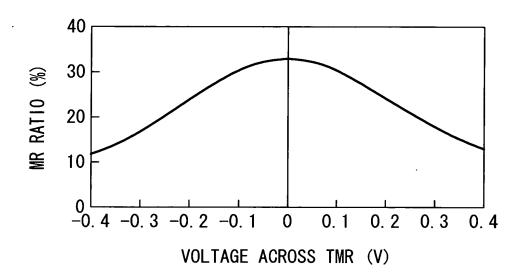


Fig. 4

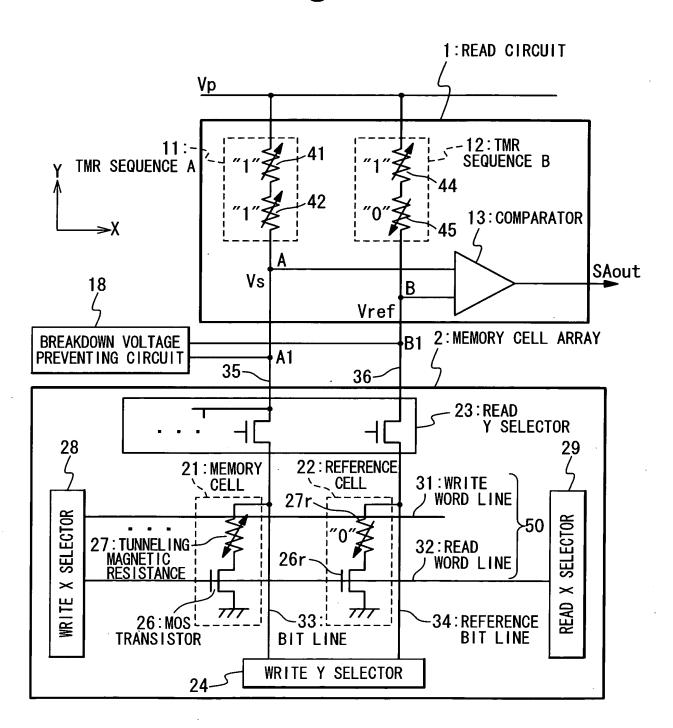


Fig. 5A Fig. 5B 10⁰ **"0"** NUMBER OF CELLS 10 10 10^{-6} Vmid Vref(ideal 10 Ro R₁ Vs (0) Vs (1) TMR RESISTANCE REFERENCE VOLTAGE Vref

Fig. 6

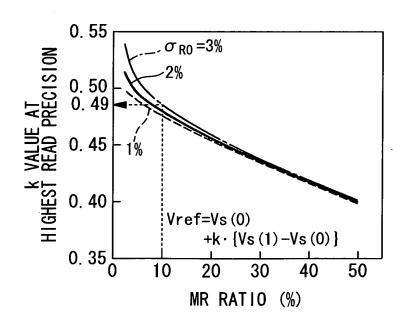


Fig. 7

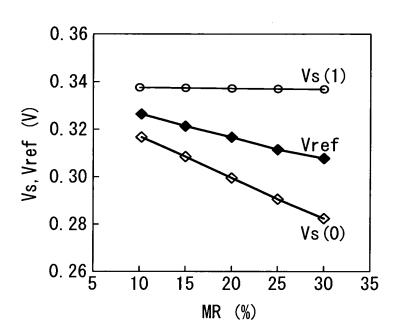


Fig. 8

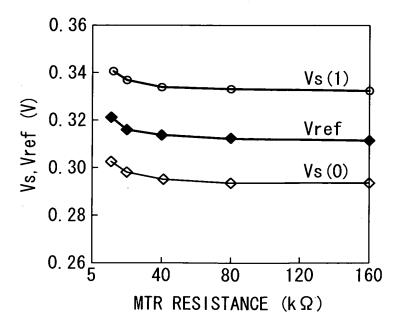


Fig. 9

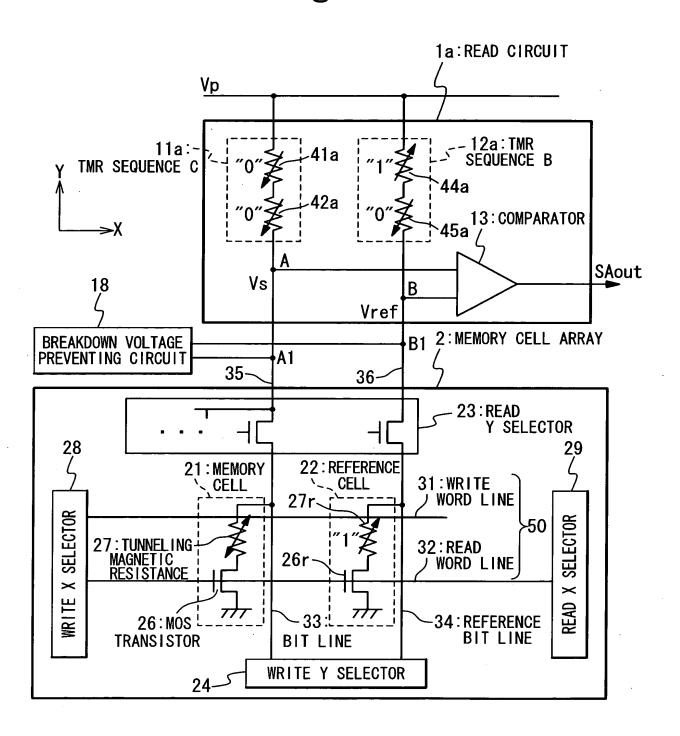


Fig. 10

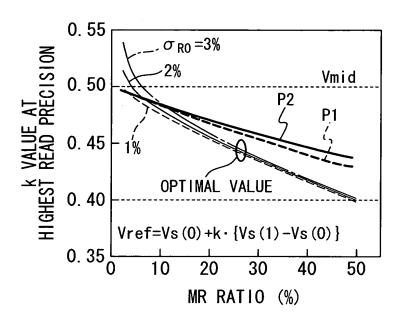


Fig. 11

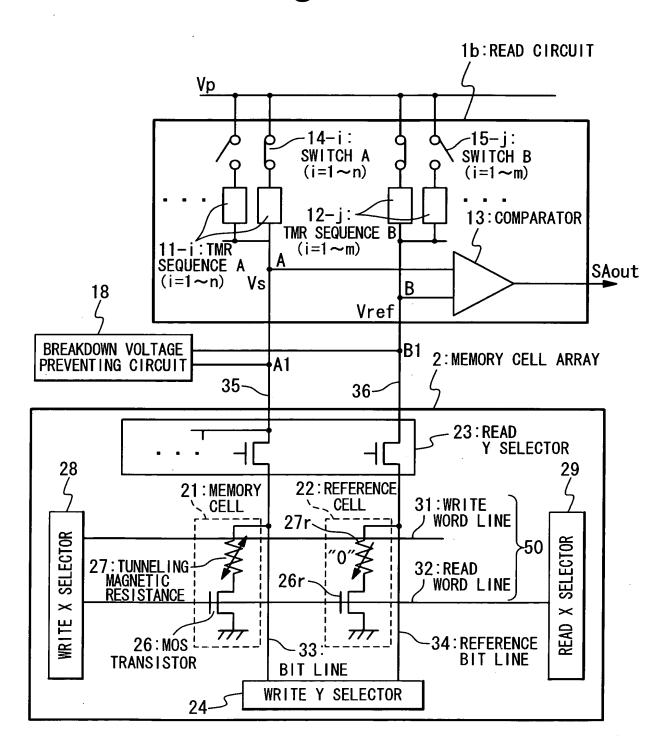
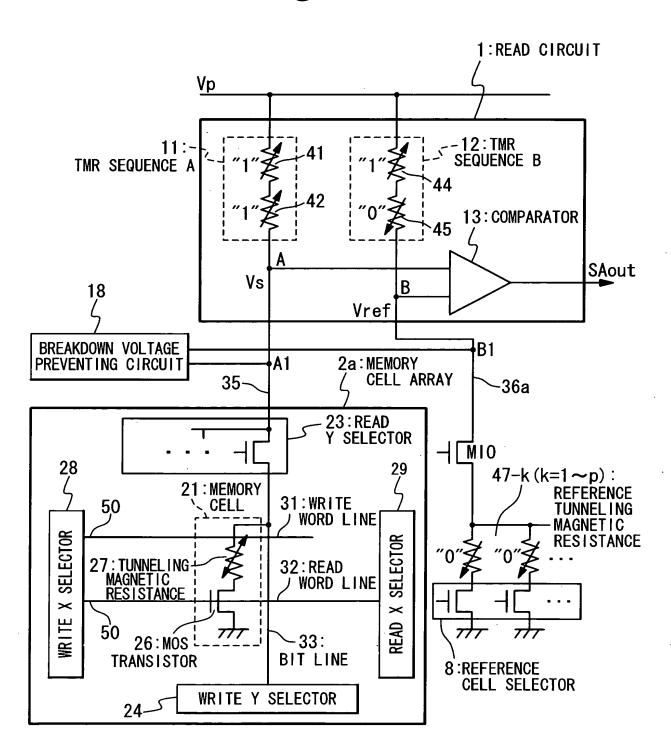


Fig. 12



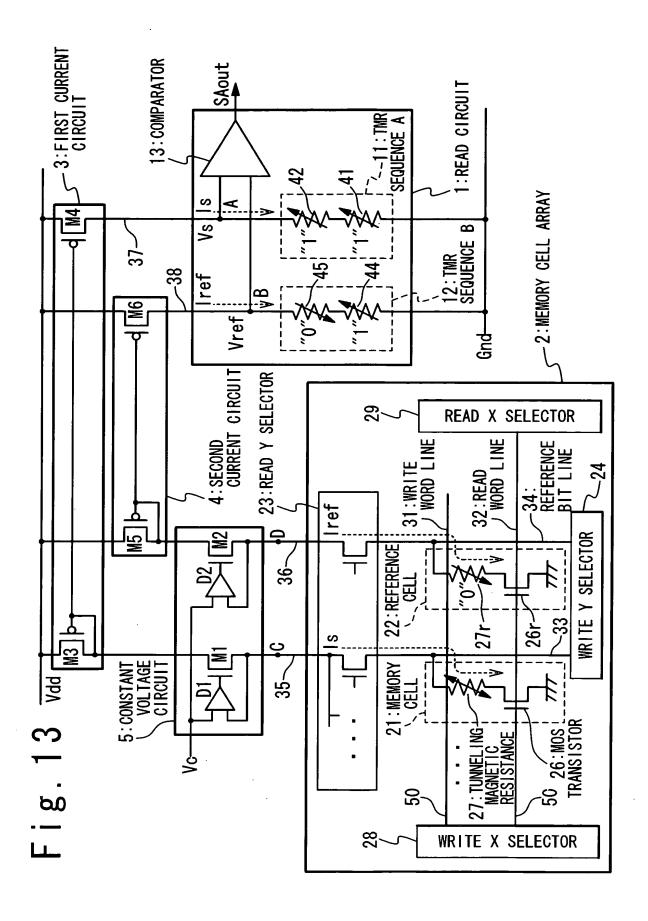


Fig. 14

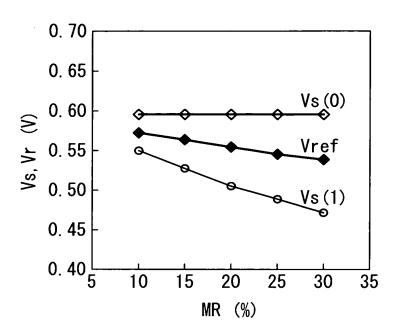
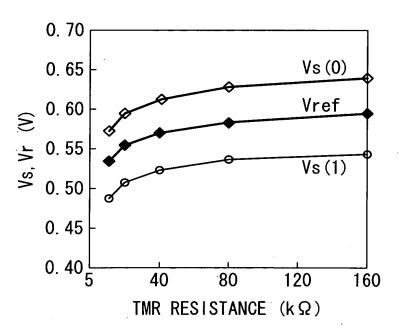
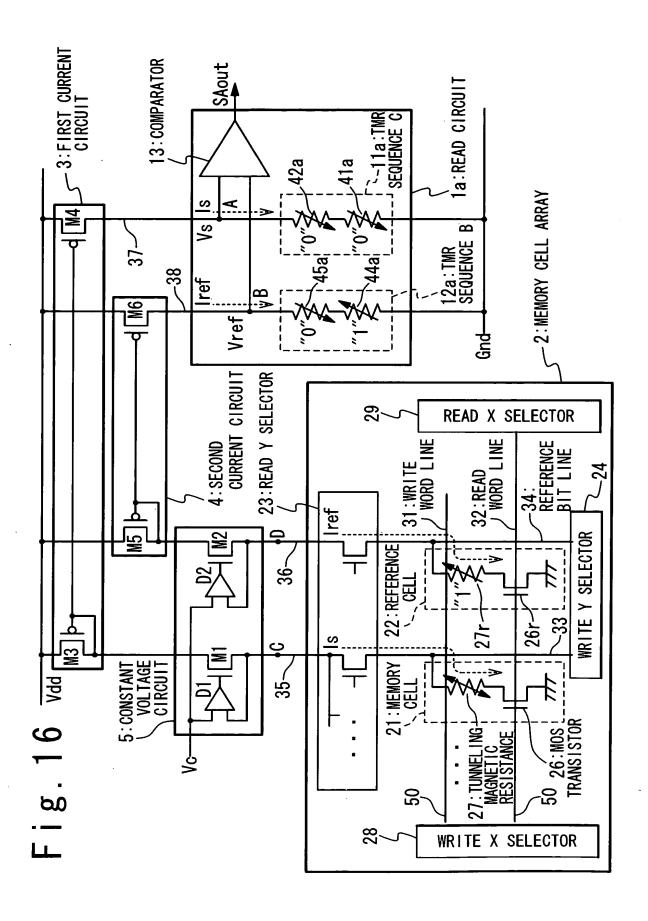
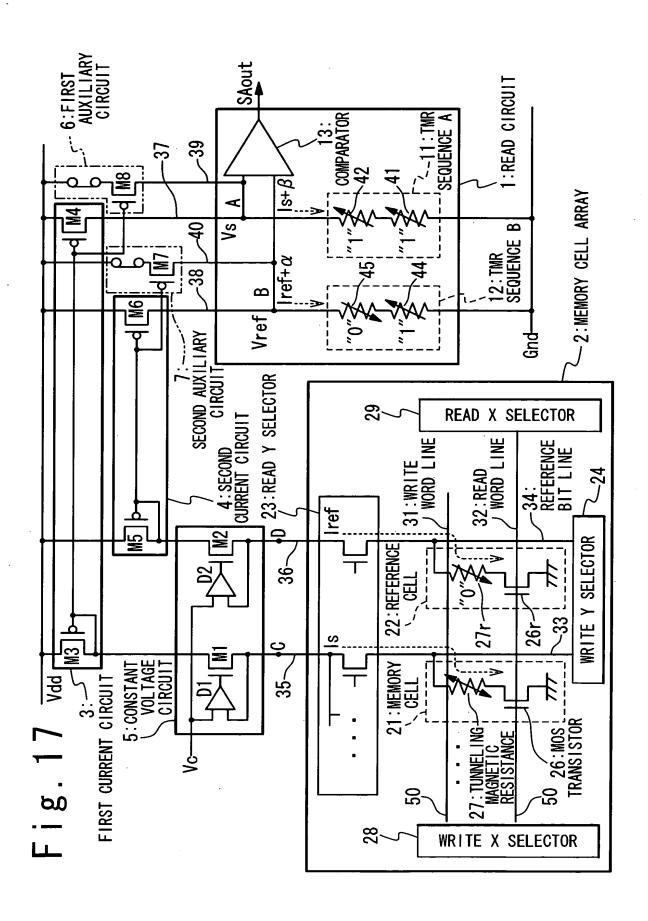
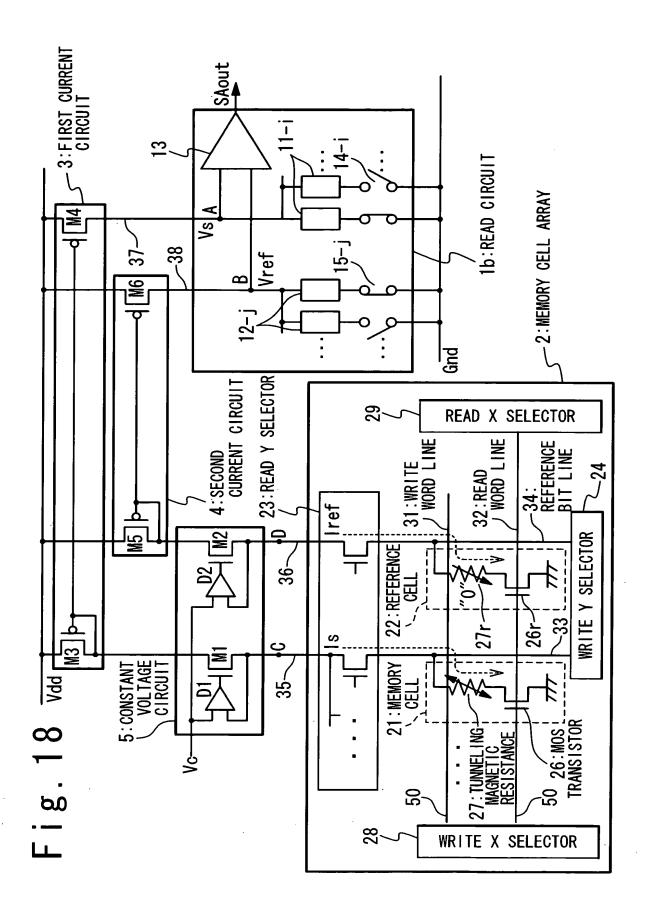


Fig. 15









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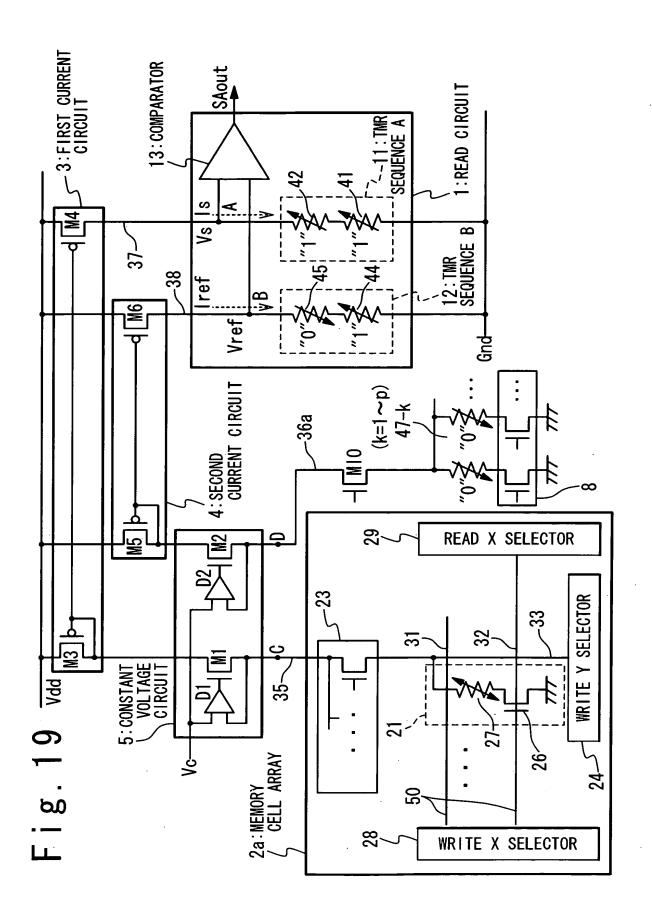


Fig. 20

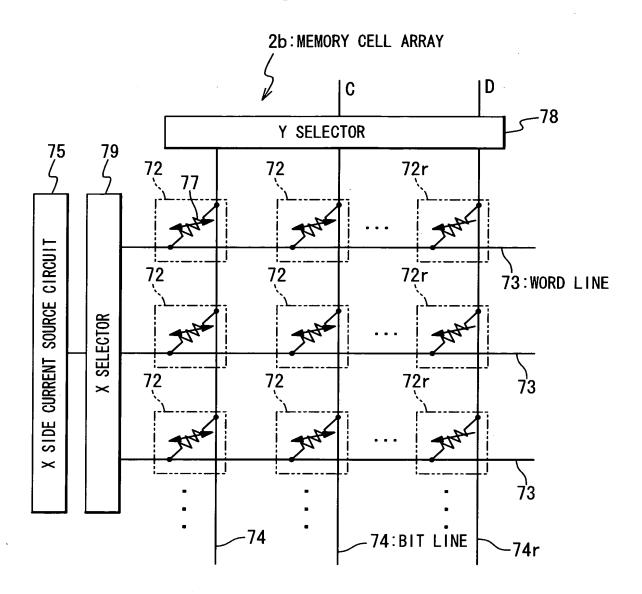




Fig. 21

